

SOP-8



Pin Definition:

- | | |
|-------------|------------|
| 1. Source 1 | 8. Drain 1 |
| 2. Gate 1 | 7. Drain 1 |
| 3. Source 2 | 6. Drain 2 |
| 4. Gate 2 | 5. Drain 2 |

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (m Ω)	I_D (A)
-30	25 @ $V_{GS} = -10V$	-7.1
	41 @ $V_{GS} = -4.5V$	-5.5

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance

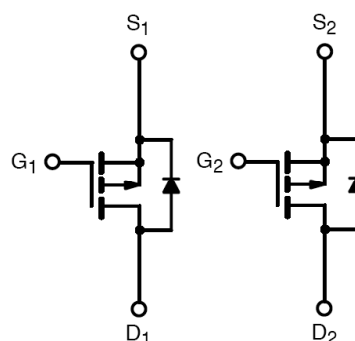
Application

- Load Switches
- Notebook PCs
- Desktop PCs

Ordering Information

Part No.	Package	Packing
TSM4925DCS RL	SOP-8	2.5Kpcs / 13" Reel

Block Diagram



Dual P-Channel MOSFET

Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-30	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	-7.1	A
Pulsed Drain Current	I_{DM}	-40	A
Continuous Source Current (Diode Conduction) ^{a,b}	I_S	-1.7	A
Maximum Power Dissipation	P_D	2.0	W
		1.3	
Operating Junction Temperature	T_J	+150	°C
Operating Junction and Storage Temperature Range	T_J, T_{STG}	- 55 to +150	°C

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Case Thermal Resistance	$R\theta_{JC}$	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	$R\theta_{JA}$	50	°C/W

Notes:

a. Pulse width limited by the Maximum junction temperature

b. Surface Mounted on FR4 Board, $t \leq 10$ sec.

Electrical Specifications (Ta = 25°C unless otherwise noted)

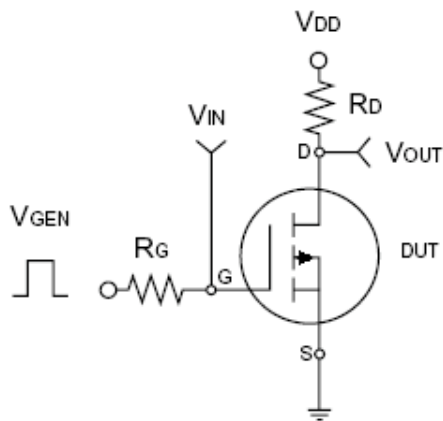
Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu A$	BV_{DSS}	-30	--	--	V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu A$	$V_{GS(TH)}$	-1	--	-3	V
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I_{GSS}	--	--	± 100	nA
Zero Gate Voltage Drain Current	$V_{DS} = -30V, V_{GS} = 0V$	I_{DSS}	--	--	-1.0	μA
On-State Drain Current ^a	$V_{DS} = -5V, V_{GS} = -10V$	$I_{D(ON)}$	-40	--	--	A
Drain-Source On-State Resistance ^a	$V_{GS} = -10V, I_D = -7.1A$	$R_{DS(ON)}$	--	20	25	m Ω
	$V_{GS} = -4.5V, I_D = -5.5A$		--	33	41	
Forward Transconductance ^a	$V_{DS} = -10V, I_D = -7.1A$	g_{fs}	--	24	--	S
Diode Forward Voltage	$I_S = -1.7A, V_{GS} = 0V$	V_{SD}	--	-0.8	-1.2	V
Dynamic ^b						
Total Gate Charge	$V_{DS} = -15V, I_D = -7.1A, V_{GS} = -10V$	Q_g	--	33	70	nC
Gate-Source Charge		Q_{gs}	--	5.8	--	
Gate-Drain Charge		Q_{gd}	--	8.6	--	
Input Capacitance	$V_{DS} = -15V, V_{GS} = 0V, f = 1.0MHz$	C_{iss}	--	1573	1900	pF
Output Capacitance		C_{oss}	--	319	--	
Reverse Transfer Capacitance		C_{rss}	--	211	295	
Switching ^c						
Turn-On Delay Time	$V_{DD} = -15V, R_L = 15\Omega, I_D = -1A, V_{GEN} = -10V, R_G = 6\Omega$	$t_{d(on)}$	--	10	15	nS
Turn-On Rise Time		t_r	--	15	25	
Turn-Off Delay Time		$t_{d(off)}$	--	110	170	
Turn-Off Fall Time		t_f	--	70	110	

Notes:

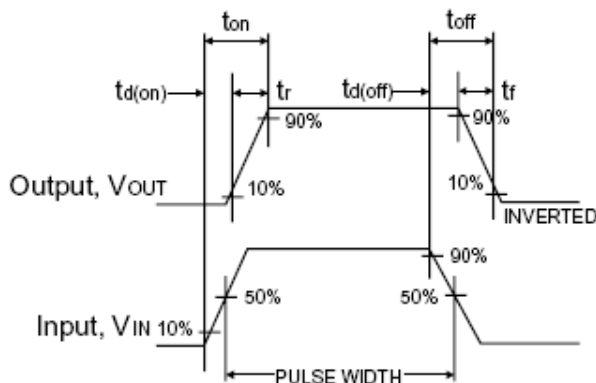
a. pulse test: PW $\leq 300\mu S$, duty cycle $\leq 2\%$

b. For DESIGN AID ONLY, not subject to production testing.

c. Switching time is essentially independent of operating temperature.



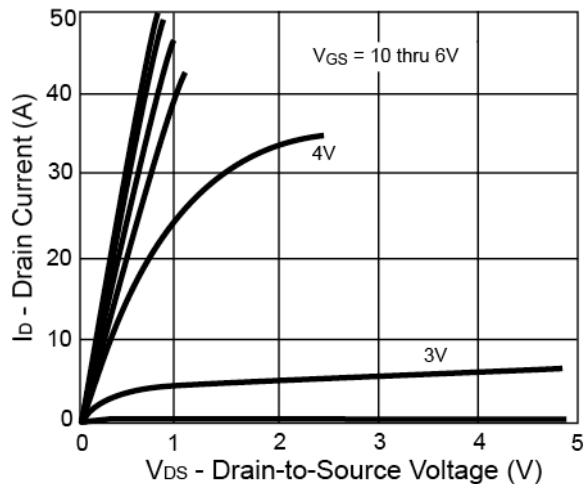
Switching Test Circuit



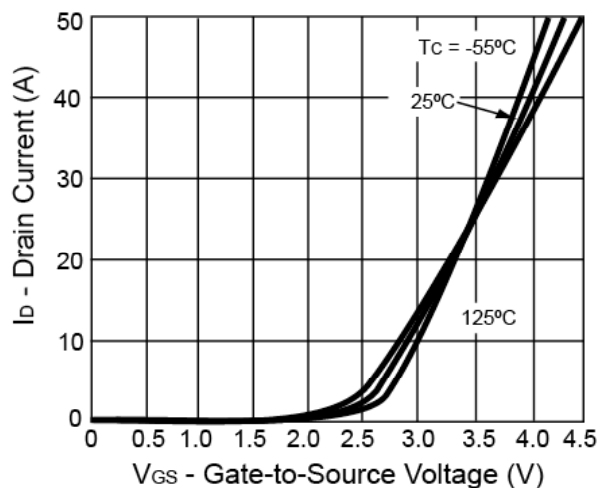
Switchin Waveforms

Electrical Characteristics Curve ($T_a = 25^\circ\text{C}$, unless otherwise noted)

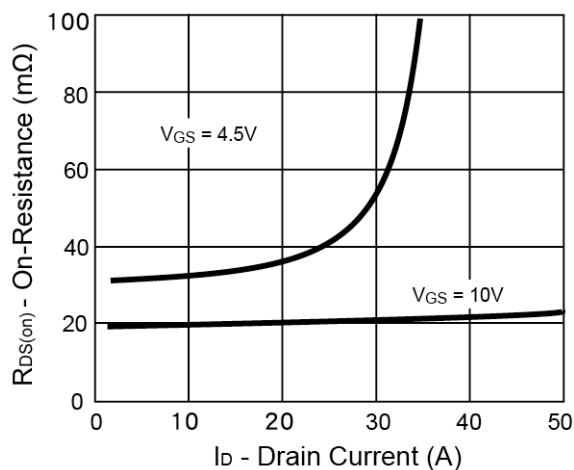
Output Characteristics



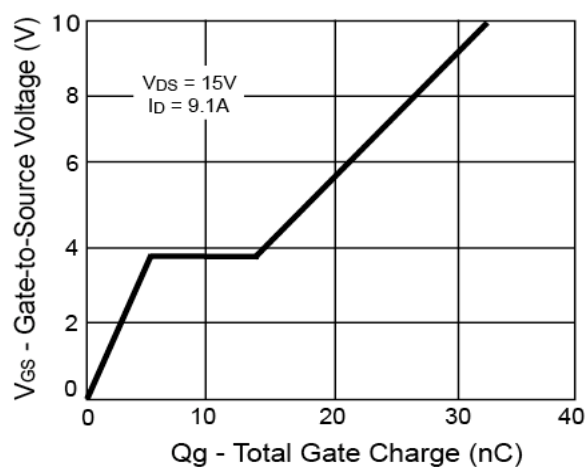
Transfer Characteristics



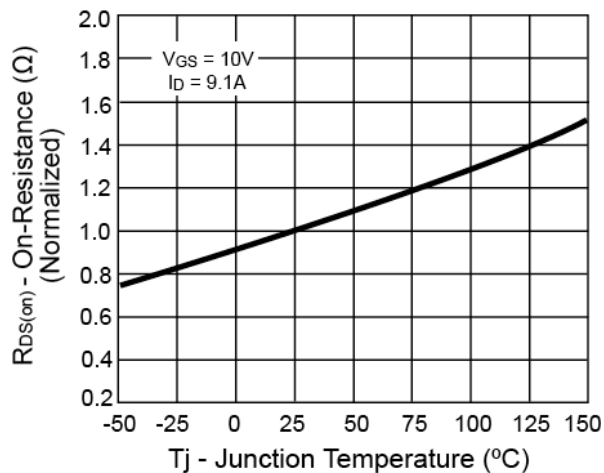
On-Resistance vs. Drain Current



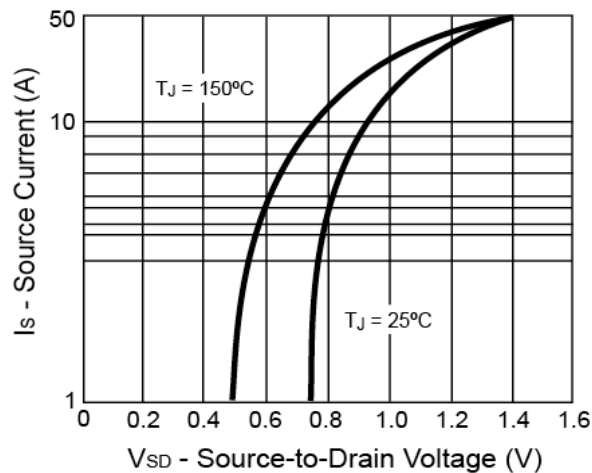
Gate Charge



On-Resistance vs. Junction Temperature

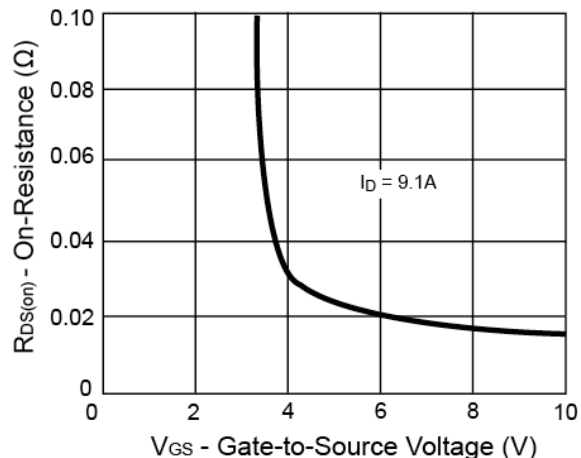


Source-Drain Diode Forward Voltage

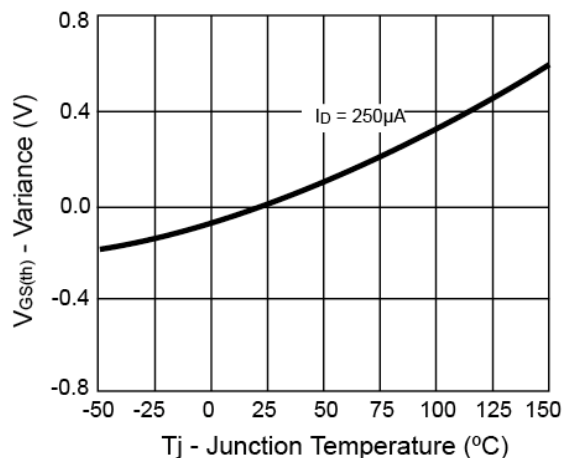


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

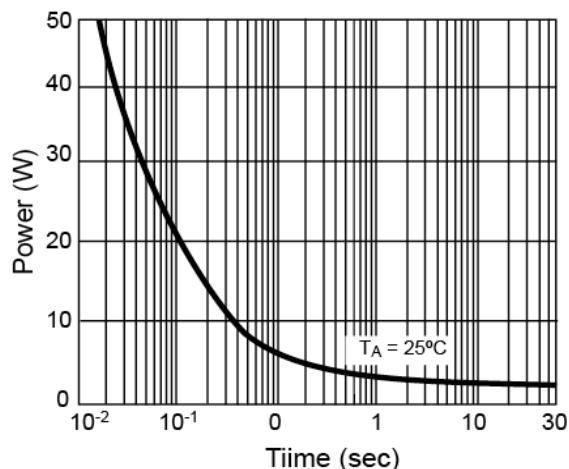
On-Resistance vs. Gate-Source Voltage



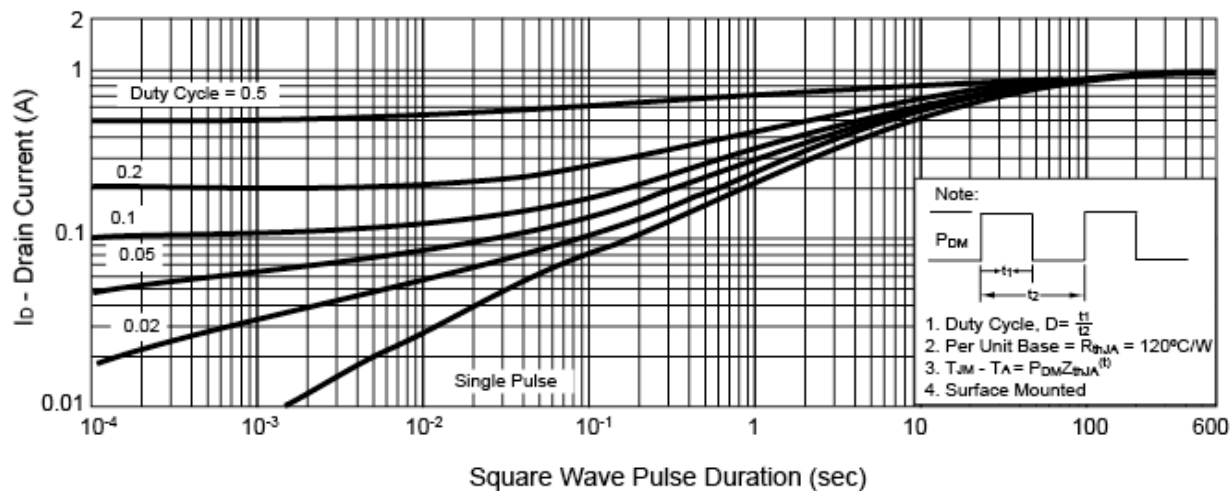
Threshold Voltage



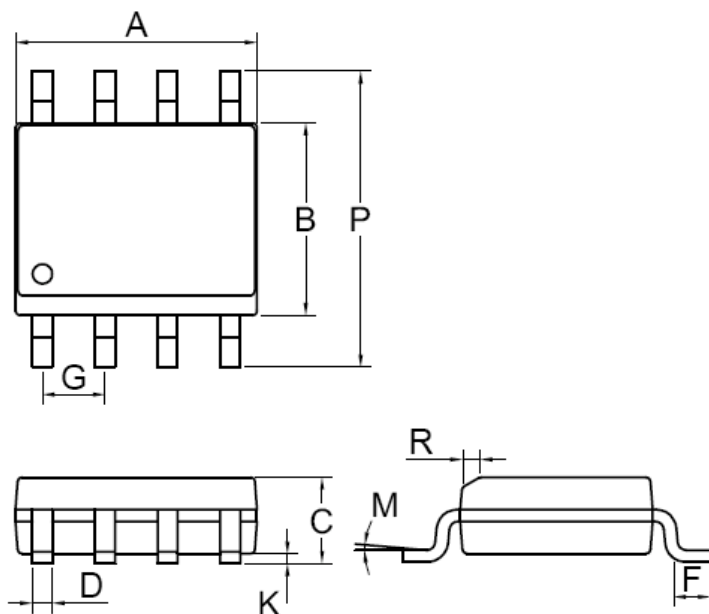
Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient

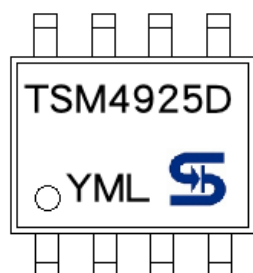


SOP-8 Mechanical Drawing



SOP-8 DIMENSION				
DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX.
A	4.80	5.00	0.189	0.196
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27BSC		0.05BSC	
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

Marking Diagram



- Y** = Year Code
M = Month Code
 (A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)
L = Lot Code

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